

L Number	Hits	Search Text	DB	Time stamp
-	44	Gan same (gaas or gallium adj arsenide) near5 substrate and 117/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 16:32
-	28	Gan same (gaas or gallium adj arsenide) near5 substrate and 117/\$.ccls. and remov\$4 near4 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 16:23
-	3	("4622083" "4727047" "4931132").PN.	USPAT	2003/08/28 16:27
-	63	Gan near5 single same remov\$4 near5 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 16:38
-	131	117/915.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 16:44
-	13	117/915.ccls. and (gan or gallium adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/28 16:40
-	19	117/915.ccls. and "iii-v"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29 13:13
-	2	20020028314.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29 13:13
-	95	((gaas or gallium near3 arsenide) near5 (sapphire or "al.sub.2o.sub.3") near5 substrate) near10 (gallium adj nitride or gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29 13:18
-	141	(gaas or gallium near3 arsenide) near5 (sapphire or "al.sub.2o.sub.3") near5 substrate same (gallium adj nitride or gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29 13:21
-	23	((gaas or gallium near3 arsenide) near5 (sapphire or "al.sub.2o.sub.3") near5 substrate same (gallium adj nitride or gan)) and 117\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29 13:21
-	38	((gaas or gallium near3 arsenide) near15 (sapphire or "al.sub.2o.sub.3") near5 substrate) same (gallium adj nitride or gan)) and 117\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29 13:26
-	9	sacrific\$4 near5 substrate near10 sapphire	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29 13:44
-	84	sacrific\$4 near5 substrate near10 (gaas or gallium near3 arsenide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/29 13:54

-	169	remov\$4 near5 substrate near10 ((gaas or gallium near3 arsenide) or (sapphire or "al.sub.2o.sub.3")) same (gallium adj nitride or gan)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/29 13:54
-	122	((gaas or gallium near3 arsenide) near5 (sapphire or "al.sub.2o.sub.3") near5 substrate same (gallium adj nitride or gan)) and 117\$.ccls.) (((gaas or gallium near3 arsenide) near15 (sapphire or "al.sub.2o.sub.3") near5 substrate) same (gallium adj nitride or gan)) and 117\$.ccls.) (sacrific\$4 near5 substrate near10 (gaas or gallium near3 arsenide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/29 13:54
-	156	(remov\$4 near5 substrate near10 ((gaas or gallium near3 arsenide) or (sapphire or "al.sub.2o.sub.3")) same (gallium adj nitride or gan)) not (((gaas or gallium near3 arsenide) near5 (sapphire or "al.sub.2o.sub.3") near5 substrate same (gallium adj nitride or gan)) and 117\$.ccls.) (((gaas or gallium near3 arsenide) near15 (sapphire or "al.sub.2o.sub.3") near5 substrate) same (gallium adj nitride or gan)) and 117\$.ccls.) (sacrific\$4 near5 substrate near10 (gaas or gallium near3 arsenide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/29 15:06